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NTE5332SM & NTE5334SM Silicon Bridge Rectifier, 1A

Features:

- Glass Passivated Die Construction
- Low Forward Voltage Drop
- High Current Capability
- High Surge Current Capability
- Designed for Surface Mount Application
- Plastic Material - UL Recognition Flammability Classification 94V-O

Maximum Ratings and Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified, Single Phase, half wave, 60Hz, resistive or inductive load. For Capacitive Load, Derate Current by 20%)

Peak Repetitive Reverse Voltage, V_{RRM}	
NTE5332SM	600V
NTE5334SM	1000V
Working Peak Reverse Voltage, V_{RWM}	
NTE5332SM	600V
NTE5334SM	1000V
DC Blocking Voltage, V_R	
NTE5332SM	600V
NTE5334SM	1000V
RMS Reverse Voltage, $V_{R(RMS)}$	
NTE5332SM	420V
NTE5334SM	700V
Average Rectified Output Current ($T_A = +40^\circ\text{C}$), I_O	1A
Non-Repetitive Peak Forward Surge Current, I_{FSM}	
(8.3ms Single Half Sine-Wave Superimposed on Rated Load)	50A
Forward Voltage per Element ($I_F = 1A$)	1.1V
Peak Reverse Current at Rated DC Blocking Voltage(Note 1), I_{RM}	
$T_A = +25^\circ\text{C}$	5 μA
$T_A = +125^\circ\text{C}$	500 μA
Typical Junction Capacitance per Element (Note 1), C_j	25pF
Operating Junction Temperature Range, T_j	-65° to +150°C
Storage Temperature Range, T_{STG}	-65° to +150°C
Typical Thermal Resistance (Per Leg, Note 2),	
Junction-to-Ambient, R_{thJA}	40°C/W
Junction-to-Case, R_{thJL}	15°C/W

Note 1. Measured at 1.0MHz and applied reverse voltage of 4.0 Volts.

Note 2 Mounted on PC bard with 13mm² copper pad.

